	Туре	Hits	Search Text	DBs	Time Stamp
├ ─¹	BRS	348	semiconductor and dielectric and (hafnium adj oxide)	SPAT; S-PGPUB; EPO; PO; DERWENT; BM TDB	2003/03/21
22	BRS	141	nductor an ric and (h and (gate ric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20
ω	BRS	1358	57/405,406,410,411.ccls 38/216,261,288,591.ccls	USPAT; US-PGPUB	2003/03/21 11:35
4	BRS	Φ 13	57/405,406,410,411.cc 8/216,261,288,591.ccl d ((hafnium adj oxide O)	USPAT; US-FGPUB	2003/03/21
U	BRS	Σ σ ,	((257/405,406,410,411.ccls.) or 438/216,261,288,591.ccls.) and ((hafnium adj oxide) or HfO)) and (dielectric with (layer or multilayer))	USPAT; US-PGPUB	2003/03/21